

### PNP -2.0A -30V Middle Power Transistor

Parameter	Value
$V_{CEO}$	-30V
I <sub>C</sub>	-2.0A

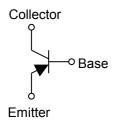
#### Features

- 1) Suitable for Middle Power Driver
- 2) Complementary NPN Types: 2SCR512P
- 3) Low V<sub>CE(sat)</sub>

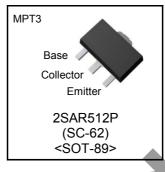
$$V_{CE(sat)} = -0.4V(Max.)$$
  
 $(I_C/I_B = -700mA/ -35mA)$ 

4) Lead Free/RoHS Compliant.

### •Inner circuit



### Outline



# Applications

Motor driver , LED driver Power supply

## Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SAR512P	MPT3	4540	T100	180	12	1,000	MB

### ◆Absolute maximum ratings (Ta = 25°C)

Parameter		Values	Unit
Collector-base voltage			V
Collector-emitter voltage			V
Emitter-base voltage		-6	V
DC	I <sub>C</sub>	-2.0	А
Pulsed	I <sub>CP</sub> *1	-4.0	А
Power dissipation		0.5	W
		2.0	W
Junction temperature		150	°C
Range of storage temperature		-55 to +150	°C
	DC	$V_{CBO}$ $V_{CEO}$ $V_{EBO}$ DC $I_{C}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

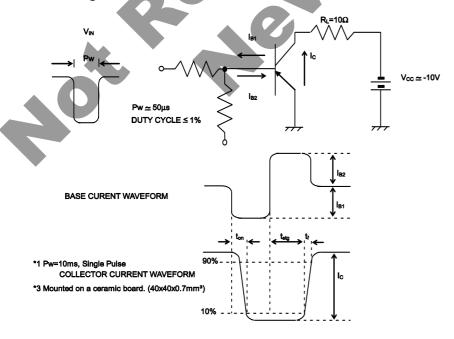
- \*1 Pw=10ms, single pulse
- \*2 Each terminal mounted on a reference land
- \*3 Mounted on a ceramic board (40×40×0.7mm)

### ●Electrical characteristics(Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -1mA	-30	-	-	V
Collector-base breakdown voltage	BV <sub>CBO</sub>	$I_{C} = -100 \mu A$	-30	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	$I_E = -100 \mu A$	-6	ı	-	V
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -30V$	ı	- 6	-1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V	-	-	-1	μΑ
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *1	$I_C = -700 \text{mA}, I_B = -35 \text{mA}$		-0.20	-0.40	V
DC current gain	h <sub>FE</sub>	$V_{CE} = -2V, I_{C} = -100 \text{mA}$	200	-	500	-
Transition frequency	f <sub>⊤</sub>	$V_{CE} = -10V, I_{E} = -100mA$ f=100MHz	_	430	-	MHz
Output capacitance	C <sub>ob</sub>	$V_{CB} = -10V, I_{E} = 0A,$ f = 1MHz		15	1	pF
Turn-on time	t <sub>on</sub> *2	I <sub>C</sub> = -1A	Ĵ	30	ı	ns
Storage time	t <sub>stg</sub> *2	I <sub>B1</sub> = -100mA I <sub>B2</sub> =100mA	-	170	-	ns
Fall time	t <sub>f</sub> *2	V <sub>CC</sub> <sup>≃</sup> −10V	-	15	-	ns

<sup>\*1</sup> Pulsed

## Switching time test circuit



<sup>\*2</sup> See switching time test circuit

### ●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

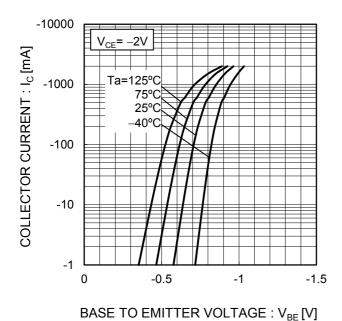
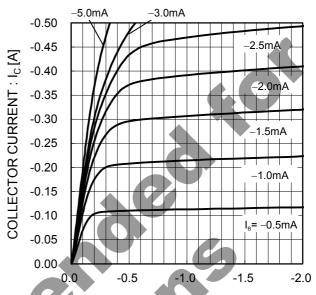


Fig.2 Typical Output Characteristics



COLECTOR TO EMITTE VOLTAGE :  $V_{CE}[V]$ 

Fig.3 DC Current Gain vs. Collector Current(I)

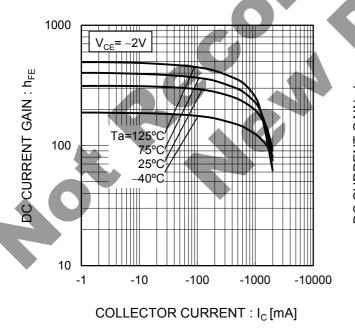
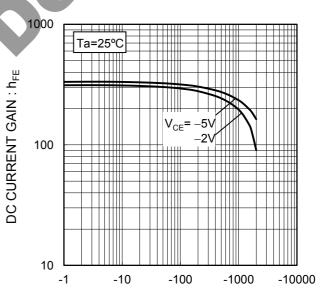


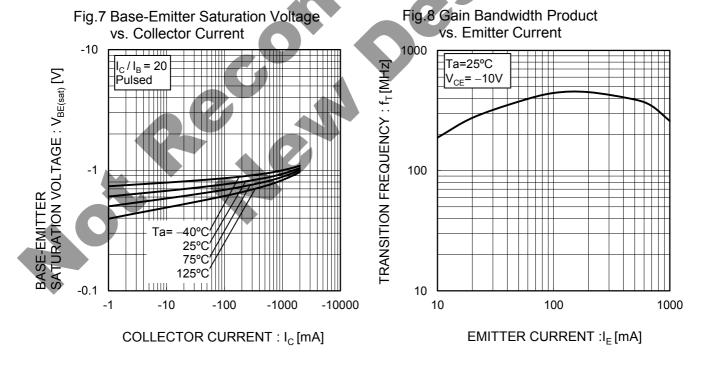
Fig.4 DC current gain vs. output current (II)



COLLECTOR CURRENT : I<sub>C</sub> [mA]

### ●Electrical characteristic curves(Ta = 25°C)

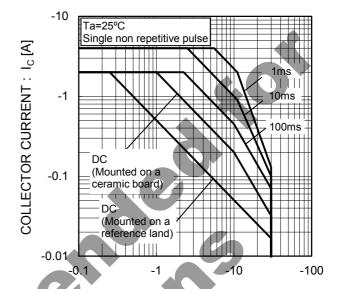
Fig.6 Collector-Emitter Saturation Voltage Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (II) vs. Collector Current (I) Ta=25°C  $I_{\rm C} / I_{\rm B} = 20$ COLLECTOR-EMITTER SATURATION VOLTAGE : V<sub>CE(sat)</sub> [V] COLLECTOR-EMITTER SATURATION VOLTAGE : V<sub>CE(sat)</sub> [V] -0.1 -0.1 = 50 Ta=125°C 10. -0.01 -0.01 75°C 25°C 40°C -0.001 -0.001 -10000 -1 -100 -1000 -100 -1000 -10000 COLLECTOR CURRENT: Ic [mA] COLLECTOR CURRENT : I<sub>C</sub> [mA]



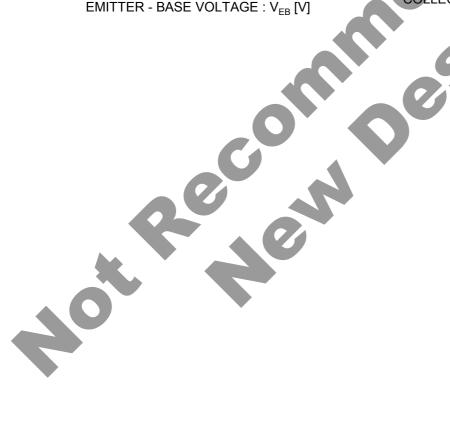
### ●Electrical characteristic curves(Ta = 25°C)

Fig.9 Emitter input capacitance vs. **Emitter-Base Voltage** Collector output capacitance vs. COLLECTOR OUTPUT CAPACITANCE: Cob [pF] Collector-Base Voltage 1000 EMITTER INPUT CAPACITANCE: Cib [pF] Ta=25°C f=1MHz I<sub>E</sub>=0A I<sub>C</sub>=0A 100  $C_{ib}$ 10 -0.1 -100 COLLECTOR - BASE VOLTAGE : V<sub>CB</sub> [V] EMITTER - BASE VOLTAGE : V<sub>FB</sub> [V]

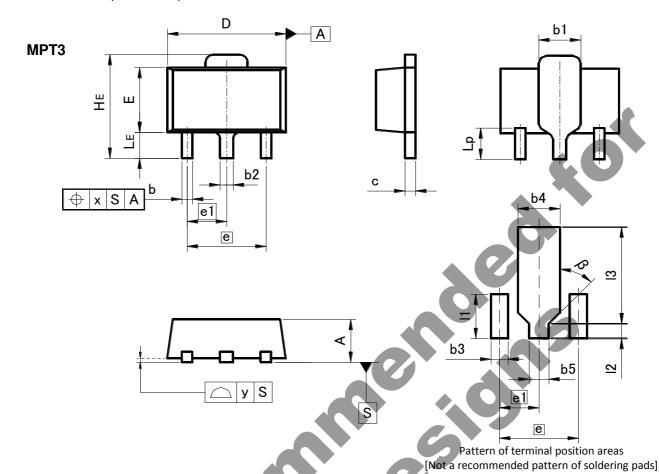
Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE: V<sub>CE</sub> [V]



## ● **Dimensions** (Unit: mm)



DIM	DIM MILIMETERS			HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.40	1.50	0.055	0.059	
b	0.30	0.50	0.012	0.020	
b1	1.50	1.70	0.059	0.067	
b2	0.40	0.60	0.016	0.024	
C	0.35	0.50	0.014	0.020	
D	4.40	4.70	0.173	0.185	
E	2.40	2.70	0.094	0.106	
е	3.0	00	0.1	18	
e1	1.	50	0.059		
HE	3.70	4.30	0.146	0.169	
LE	0.80	1.20	0.031	0.047	
Lp	1.01	1.41	0.040	0.056	
X		0.15	_	0.006	
У		0.10	_	0.004	

DIM	MILIMI	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b3	_	0.65	-	0.026	
b4	-	1.70	-	0.067	
b5	-	0.75	-	0.030	
11	-	1.71	1	0.067	
12	-	0.58	1	0.023	
13	_	3.72	_	0.146	
β	45°		45°		

Dimension in mm / inches

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